

AMENDMENTS TO THE SPECIFICATION:

Page 3:

Please substitute the following paragraph for the paragraph beginning at line 6:

The inventors of the present invention have been dedicated to study and development related to nonvolatile semiconductor memories. After considering the above-stated technique, the inventors were faced with a problem that regarding time required to reach a deletion potential (time required to pull out a desired quantity of electrons).

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Please substitute the following paragraph for the paragraph beginning at line 5:

Accordingly, it takes certain time for the voltage (VN<sub>i</sub>S) of the separation region NiSO and the voltage (VMC<sub>0</sub>) of the p type well PWL<sub>0</sub> to become 10V, respectively. In this case, a current to the separation region NiSO in a forward direction by the voltage of the p type well PWL<sub>0</sub> and the potential of the separation region NiSO becomes a voltage supplied to the p type well PWL<sub>0</sub>.